

# Millisecond-range electron spin memory in singly-charged InP quantum dots

Bipul Pal,<sup>1,\*</sup> Michio Ikezawa,<sup>1</sup> Yasuaki Masumoto,<sup>1</sup> and Ivan V. Ignatiev<sup>1,2</sup>

<sup>1</sup>*Institute of Physics, University of Tsukuba, Tsukuba 305-8571, Japan*

<sup>2</sup>*Institute of Physics, St. Petersburg State University, St.-Petersburg 198504, Russia*

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We report millisecond-range spin memory of resident electrons in an ensemble of InP quantum dots (QDs) under a small magnetic field of 0.1 T applied along the optical excitation axis at temperatures up to about 5 K. A pump-probe photoluminescence (PL) technique is used for optical orientation of electron spins by the pump pulses and for study of spin relaxation over the long time scale by measuring the degree of circular polarization of the probe PL as a function of pump-probe delay. Dependence of spin decay rate on magnetic field and temperature suggests two-phonon processes as the dominant spin relaxation mechanism in this QDs at low temperatures.

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Electron spin in semiconductors may be suitable for use as a quantum memory in quantum repeaters as semiconductors are capable of converting photons to electrons (and holes) while transferring quantum information from photon polarization to electron spin, and vice versa.<sup>1</sup> However, a long spin relaxation time ( $\tau_s$ ) is necessary to realize spin quantum memory. In semiconductor quantum dots (QDs)  $\tau_s$  up to a few ms was theoretically predicted as a result of suppression of important spin relaxation mechanisms due to 3D confinement and lack of energy dispersion.<sup>2,3,4</sup> This has stimulated experimental investigations of long spin memory in QDs.<sup>5,6,7,8,9,10,11</sup> For example, electron spin relaxation time of about 200  $\mu$ s in InGaAs vertical QDs<sup>6</sup> at  $T \leq 0.5$  K and zero external magnetic field ( $B$ ), about 0.85 ms in electrically gated GaAs lateral QDs<sup>7</sup> at  $T < 0.3$  K and  $B = 8$  T, and about 20 ms in self-assembled InGaAs QDs<sup>8</sup> at  $T = 1$  K and  $B = 4$  T has been recently reported. Many of the previous results of long spin memory in QDs were obtained in InGaAs and GaAs QDs under special condition of low temperature ( $\leq 1$  K) and large magnetic field ( $\geq 4$  T).

In this letter we report observation of optically created electron spin-orientation surviving up to about 1 ms in an ensemble of singly negatively charged InP QDs at  $B = 0.1$  T applied along the optical excitation axis at  $T \sim 5$  K. The sample consists of a single layer of self-assembled InP QDs embedded between GaInP barriers. The average base diameter (height) of the QDs is about 40 (5) nm with an areal density  $\sim 10^{10}$  cm<sup>-2</sup>. We use a pump-probe PL technique<sup>5,10,11</sup> to study electron spin orientation dynamics by measuring the circular polarization [defined as  $P = (I^{++} - I^{+-})/(I^{++} + I^{+-})$ , where  $I^{++(-)}$  is the PL intensity for excitation with  $\sigma^+$  probe and detection of  $\sigma^{+(-)}$  probe PL] of the probe pulse PL in presence of a preexcitation by a pump pulse. Our experimental setup is schematically shown in Fig. 1(a).

A CW Ti:sapphire laser beam is split into pump and probe beams. Two acousto-optic modulators (AOM) driven by programmable function generator (PFG) generates pump and probe pulses with controllable pulse width and delay ( $\tau$ ) between them. Glan-Thompson polarizers (GTP) and wave plates are used to control

the circular polarization of the pump and probe beams. The PL signal is sent through a combination of a photoelastic modulator (PEM) and a GTP before dispersing in a monochromator and detecting in a GaAs photomultiplier tube (PMT). The PMT output is connected to a two-channel gated photon counter (GPC). The PEM acts as an oscillating  $\lambda/4$ -plate and when combined with GTP, allows detection of PL intensity in the  $\sigma^+$  and  $\sigma^-$  channels. The PEM frequency,  $f_P = 42$  kHz, is reduced to  $f_T = f_P/(n + 0.5)$  (typically  $n = 40$  in our measurements) to trigger the PFG and GPC.<sup>12</sup> Thus, one probe pulse (and A-gate of the GPC) is centered at the  $+\lambda/4$  and the next probe pulse (and B-gate of the GPC) is centered at the  $-\lambda/4$  retardation peaks of the PEM [Fig. 1(b)]. We typically use a GPC gate width of 5  $\mu$ s, while the pump (probe) pulse width is 60 (3)  $\mu$ s, giving a pump (probe) power density [ $W_{\text{pump (probe)}}$ ] of about 0.5 (0.05) W cm<sup>-2</sup>. The low probe power density ensures that the pump-induced spin polarization is not fully erased by the probe pulse. The excitation energy is tuned to about 1.771 eV (below-barrier, QD excited state excitation) and the QD ground state PL is detected at about 1.729 eV. An external electric bias of  $U_{\text{bias}} = -0.1$  V is applied to the sample. We find that under this condition the PL polarization is negative and reaches maximum.<sup>11</sup> A study of trionic quantum beats in this sample<sup>13</sup> showed that at  $U_{\text{bias}} \approx -0.1$  V each QD contains one resident electron on an average. This suggests that the negative PL polarization arises from trionic state, as is discussed e.g., in Refs. 5,9,14,15.

In our experiments, a  $\sigma^+$  (or  $\sigma^-$ ) polarized pump induces  $\downarrow$  (or  $\uparrow$ ) spin orientation of the resident electrons.<sup>16</sup> A probe pulse, variably delayed with respect to the pump pulse, tests this pump-induced spin-orientation. The probe beam (always  $\sigma^+$  polarized) creates a hot trion with *parallel* [ $\downarrow\downarrow$ -QDs] or *anti-parallel* [ $\uparrow\downarrow$ -QDs] electron spins. After a flip-flop process in  $\downarrow\downarrow$ -QDs shown schematically in Fig. 2(a), the probe PL polarization becomes negative,<sup>11</sup> while it is positive for the  $\uparrow\downarrow$ -QDs [Fig. 2(b)]. At any given  $\tau$  the net probe PL polarization is determined by the ratio of  $\downarrow\downarrow$ - and  $\uparrow\downarrow$ -QDs.

We measure the probe PL polarization for (i) co-



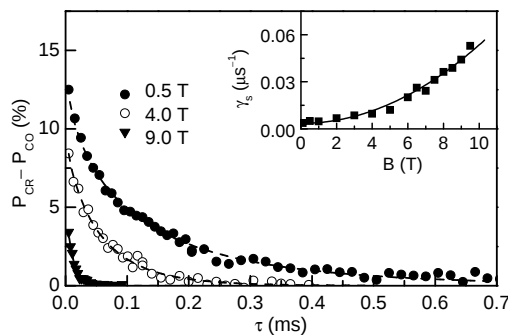


FIG. 4: Delay dependence of  $P_{CR} - P_{CO}$  at a few  $B$ .  $T = 2$  K,  $U_{bias} = -0.1$  V,  $W_{pump} (probe) = 0.5$  (0.05)  $W\text{ cm}^{-2}$ . Dashed lines are stretched exponential fits (discussed in the text). Inset shows spin decay rate ( $\gamma_s$ ) as a function of  $B$ .

We now present the magnetic field dependence of the spin decay process. Decay of  $P_{CR} - P_{CO}$  at a few values of  $B$  at  $T = 2$  K is shown in Fig. 4. We find that the decay becomes increasingly faster with increase in  $B$ . An effective spin decay rate obtained from stretched exponential fit to the data is plotted as a function of  $B$  in the inset of Fig. 4. Decay rate  $\gamma_s$  is found to increase superlinearly with  $B$ . Several possible mechanisms for such an increase are discussed in the literature.<sup>3,4,26</sup> Magnetic field couples the higher energy states with nonzero orbital momentum to the electron spin states split by the magnetic field (Zeeman splitting) that allows a small admixture of the states of opposite spin to each Zeeman sublevel.<sup>3,4</sup> At low temperature this enables spin-flip transition between Zeeman sublevels via participation of acoustic phonons to dissipate energy (one-phonon resonant process). With increasing  $B$  the Zeeman splitting increases. Due to higher density of resonant phonons at increased energy

and more efficient mixture of the states by the magnetic field, the spin relaxation rate increases. Theoretical calculations<sup>3,4</sup> have predicted  $\gamma_s \sim B^5$  at very low temperature and large magnetic field if the spin-orbit interaction and the one-phonon scattering dominate. However, for  $T$  of about a few kelvin, the two-phonon nonresonant (Raman) scattering may become important.<sup>4</sup> In that case, the magnetic field dependence is only determined by the admixture of the excited states and becomes quadratic.<sup>3</sup> Our data in Fig. 4-inset can be fitted very well with  $\gamma_s = \alpha + \beta B^2$ . This argues for the two-phonon scattering as the main mechanism of acceleration of the spin relaxation in magnetic field.

The acceleration of spin relaxation could also result from hyperfine interaction.<sup>26</sup> However, this is unlikely in our case due to very small nuclear spin polarization in the InP QDs<sup>22,23</sup> we studied.

In conclusion, we have observed long spin memory, persisting over 1 ms, in an ensemble of singly negatively charged InP QDs at small magnetic field (0.1 T) and at moderate temperature ( $\sim 5$  K). Our data on the magnetic field and temperature dependence of spin decay rate suggests two-phonon scattering may be the dominant spin relaxation mechanism. Long spin memory observed here in III-V semiconductor QDs is relevant for quantum information communication and storage. Though our study is made at about  $0.7\text{ }\mu\text{m}$  wavelength ( $\lambda$ ), III-V semiconductor system can be easily adapted to  $\lambda = 1.3$  and  $1.5\text{ }\mu\text{m}$ , suitable for fiber optic communication.

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\* E-mail: bipulpal@sakura.cc.tsukuba.ac.jp  
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